

1SS81

Silicon Epitaxial Planar Diode for High Voltage Switching

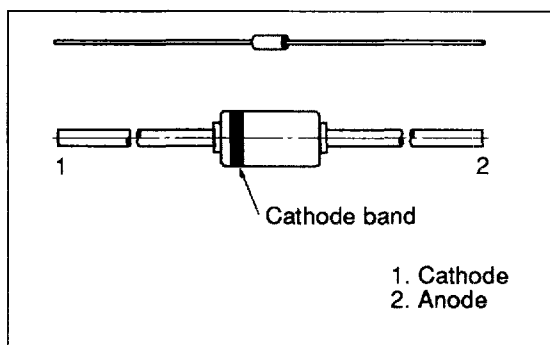
Features

- High reverse voltage. ($V_R=150V$)
- High reliability with glass seal.

Ordering Information

Type No.	Cathode band	Package Code
1SS81	Verdure	DO-35

Outline



Absolute Maximum Ratings ** ($T_a = 25^\circ C$)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}^*	200	V
Reverse voltage	V_R	150	V
Peak forward current	I_{FM}	625	mA
Non-Repetitive peak forward surge current	I_{FSM}^{**}	1	A
Average forward current	I_o	200	mA
Power dissipation	P_d	400	mW
Junction temperature	T_j	175	$^\circ C$
Storage temperature	T_{stg}	-65 to +175	$^\circ C$

* Reverse voltage in excess of peak reverse voltage may deteriorate electrical characteristic.

** Within 1s forward surge current.

Electrical Characteristics ($T_a = 25^\circ C$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	$I_F = 100 \text{ mA}$
Reverse current	I_{R1}	—	—	0.2	μA	$V_R = 150 \text{ V}$
	I_{R2}	—	—	100		$V_R = 200 \text{ V}$
Capacitance	C	—	1.5	—	pF	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$
Reverse recovery time	t_{rr}	—	—	100	ns	$I_F=I_R=30\text{mA}, I_{rr}=3\text{mA}, R_L=100\Omega$

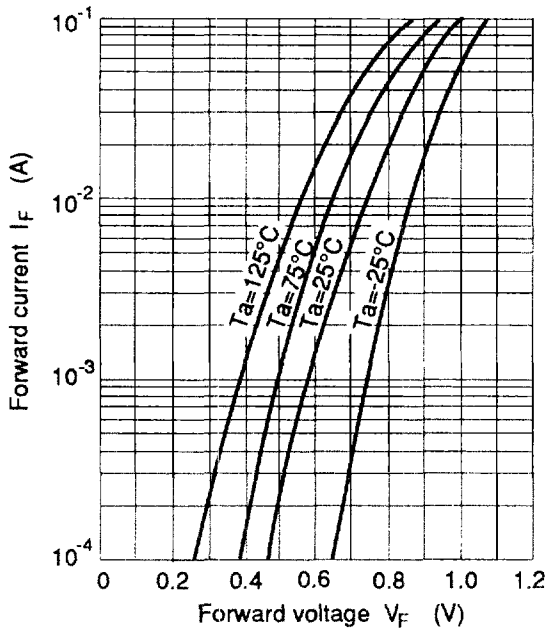


Fig.1 Forward current Vs. Forward voltage

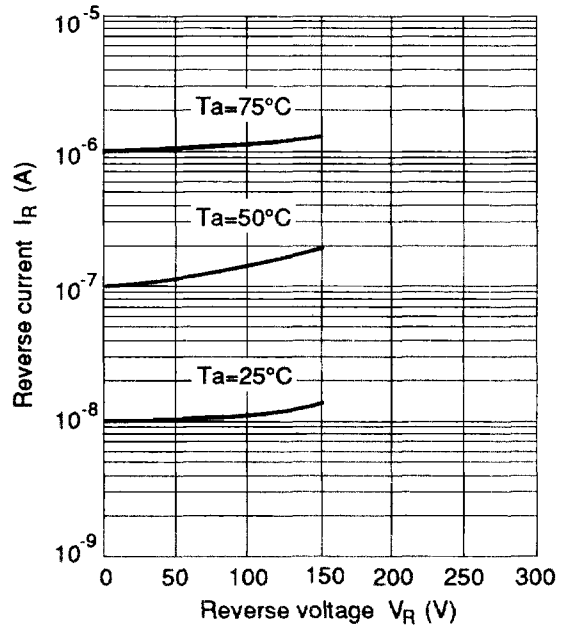


Fig.2 Reverse current Vs. Reverse voltage

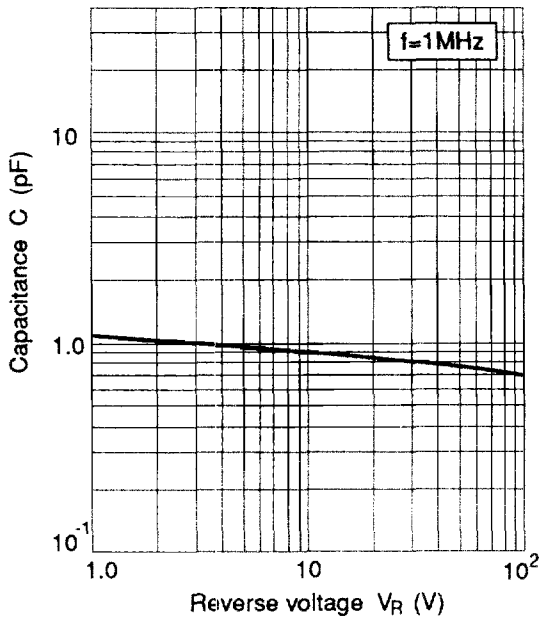


Fig.3 Capacitance Vs. Reverse voltage